



**FUKUCOM COMPANY LTD.**

**福 靈 有 限 公 司**

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

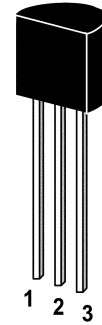
## ST 2SC1740

### NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups Q, R, S and E. according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

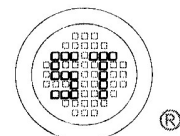


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package  
Weight approx. 0.19g

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	60	V
Collector Emitter Voltage	$V_{CEO}$	50	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	150	mA
Power Dissipation	$P_{tot}$	300	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-55 to +150	$^\circ\text{C}$



**SEMTECH**

Dated : 07/12/2002



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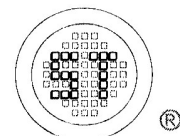
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### Characteristics at $T_{amb}=25^{\circ}C$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE}=6V, I_C=1mA$	Q	$h_{FE}$	120	-	270	-
	R	$h_{FE}$	180	-	390	-
	S	$h_{FE}$	270	-	560	-
	E	$h_{FE}$	390	-	820	-
Collector Base Breakdown Voltage at $I_C=50\mu A$	$V_{(BR)CBO}$	60	-	-	V	
Collector Emitter Breakdown Voltage at $I_C=1mA$	$V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $I_E=50\mu A$	$V_{(BR)EBO}$	5	-	-	V	
Collector Cutoff Current at $V_{CB}=60V$	$I_{CBO}$	-	-	0.1	$\mu A$	
Emitter Cutoff Current at $V_{EB}=5V$	$I_{EBO}$	-	-	0.1	$\mu A$	
Collector Saturation Voltage at $I_C=50mA, I_B=5mA$	$V_{CE(sat)}$	-	-	0.4	V	
Gain Bandwidth Product at $V_{CE}=12V, I_C=2mA$	$f_T$	-	180	-	MHz	
Output Capacitance at $V_{CB}=12V, f=1MHz$	$C_{OB}$	-	2	3.5	pF	



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